查询"2N6429"供应商

Central
Semiconductor Corp.
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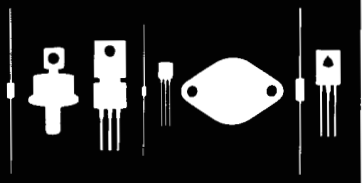
145 Adams Avenue
Hauppauge, New York 11788



2N6428
2N6429

NPN SILICON TRANSISTOR

JEDEC TO-92 CASE (EBC)

DESCRIPTION

The CENTRAL SEMICONDUCTOR 2N6428, 2N6429 types are NPN Silicon Transistors manufactured by the epitaxial planar process, designed for high gain amplifier applications.

MAXIMUM RATINGS ($T_A = 25^oC$)

	SYMBOL	2N6428	2N6429	UNITS
Collector-Base Voltage	V_{CBO}	60	55	V
Collector-Emitter Voltage	V_{CEO}	50	45	V
Emitter-Base Voltage	V_{EBO}	6.0		V
Collector Current	I_C	200		mA
Power Dissipation	P_D	625		mW
Power Dissipation ($T_C = 25^oC$)	P_D	1.5		W
Operating and Storage Junction Temperature	T_J, T_{stg}	-65 to +150		^oC
Thermal Resistance	Θ_{JA}	200		$^oC/W$
Thermal Resistance	Θ_{JC}	83.3		$^oC/W$

ELECTRICAL CHARACTERISTICS ($T_A = 25^oC$ unless otherwise noted)

		2N6428		2N6429		
SYMBOL	TEST CONDITIONS	MIN	MAX	MIN	MAX	UNITS
I_{CBO}	$V_{CB} = 30V$		10		10	nA
I_{CEO}	$V_{CE} = 30V$		25		25	nA
I_{EBO}	$V_{BE} = 5.0V$		10		10	nA
BV_{CBO}	$I_C = 100\mu A$	60		55		V
BV_{CEO}	$I_C = 1.0mA$	50		45		V
$V_{CE(SAT)}$	$I_C = 10mA$, $I_B = 0.5mA$		0.20		0.20	V
$V_{CE(SAT)}$	$I_C = 100mA$, $I_B = 5.0mA$		0.60		0.60	V
$V_{BE(ON)}$	$V_{CE} = 5.0V$, $I_C = 1.0mA$	0.56	0.66	0.56	0.66	V
h_{FE}	$V_{CE} = 5.0V$, $I_C = 10\mu A$	250		500		
h_{FE}	$V_{CE} = 5.0V$, $I_C = 100\mu A$	250	650	500	1250	
h_{FE}	$V_{CE} = 5.0V$, $I_C = 1.0mA$	250		500		
h_{FE}	$V_{CE} = 5.0V$, $I_C = 10mA$	250		500		
f_T	$V_{CE} = 5.0V$, $I_C = 1.0mA$, $f = 100MHz$	100	700	100	700	MHz
C_{ob}	$V_{CB} = 10V$, $I_E = 0$, $f = 1.0MHz$		3.0		3.0	pF
C_{ib}	$V_{BE} = 0.5V$, $I_C = 0$, $f = 1.0MHz$		8.0		8.0	pF
h_{ie}	$V_{CE} = 5.0V$, $I_C = 1.0mA$, $f = 1.0kHz$	3.0	30	6.0	60	kΩ
h_{re}	$V_{CE} = 5.0V$, $I_C = 1.0mA$, $f = 1.0kHz$	2.0	20	5.0	50	$X\ 10^{-4}$
h_{fe}	$V_{CE} = 5.0V$, $I_C = 1.0mA$, $f = 1.0kHz$	200	800	400	1600	
h_{oe}	$V_{CE} = 5.0V$, $I_C = 1.0mA$, $f = 1.0kHz$	5.0	50	10	100	μmhos